Unit in mm

TOSHIBA TRANSISTOR SILICON PNP TRIPLE DIFFUSED TYPE

2 S B 1 6 4 2

AUDIO FREQUENCY POWER AMPLIFIER APPLICATIONS

• Low Collector Saturation Voltage

: $V_{CE} (sat) = -1.5V (Max.) (I_C = -2.5A, I_B = -0.25A)$

• Collector Power Dissipation : P_C=25W (T_c=25°C)

• Collector Metal (Fin) is Fully Covered with Mold Resin

MAXIMUM RATINGS (Tc = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT	
Collector-Base Voltage	v_{CBO}	-60	V	
Collector-Emitter Voltage	v_{CEO}	-60	V	
Emitter-Base Voltage	$V_{ m EBO}$	-7	V	
Collector Current	$I_{\mathbf{C}}$	-4	A	
Base Current	$I_{\mathbf{B}}$	-1	A	
Collector Power Ta=25°C	Da	2.0	w	
Dissipation Tc=25°C	P_{C}	25	**	
Junction Temperature	T_{j}	150	°C	
Storage Temperature Range	$\mathrm{T_{stg}}$	-55~150	$^{\circ}\mathrm{C}$	

1. BASE 2. COLLECTOR 3. EMITTER JEDEC JEITA 93.2±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2 2.7±0.2

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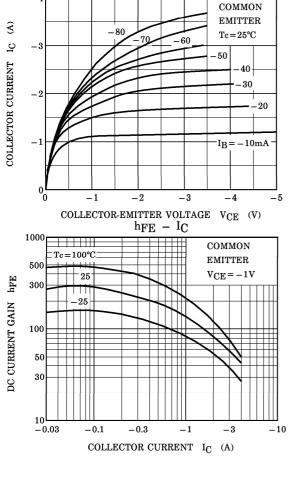
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TOSHIBA

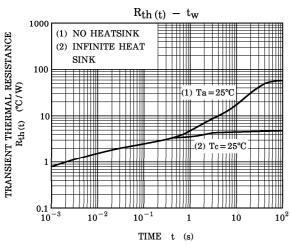
ELECTRICAL CHARACTERISTICS (Tc = 25°C)

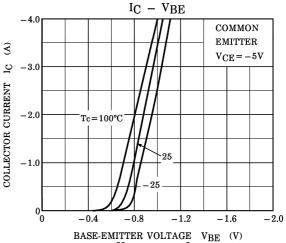
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	ICBO	$V_{CB} = -60V, I_{E} = 0$	_	_	-10	μ A
Emitter Cut-off Current	I_{EBO}	$V_{EB} = -7V, I_{C} = 0$	_	_	-10	μ A
Collector-Emitter Breakdown Voltage	V (BR) CEO	$I_C = -10 \text{mA}, I_B = 0$	-60	_	_	V
DC Current Gain	h _{FE} (1)	$V_{CE} = -5V, I_{C} = -0.5A$	100	_	320	
	h _{FE} (2)	$V_{CE} = -5V$, $I_{C} = -3A$	20	_		
Collector-Emitter Saturation Voltage	V _{CE} (sat)	$I_C = -2.5A, I_B = -0.25A$	_	-0.7	-1.5	V
Base-Emitter Voltage	$ m V_{BE}$	$V_{CE} = -5V, I_{C} = -0.5A$	_	-0.75	-1.0	V
Transition Frequency	$ m f_{T}$	$V_{CE} = -5V, I_{C} = -0.5A$	_	9	_	MHz
Collector Output Capacitance	Cob	$V_{CB} = -10V, I_{E} = 0, f = 1MHz$	_	50	_	рF

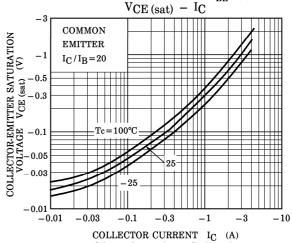
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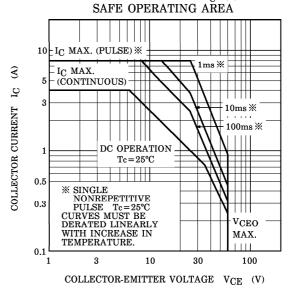


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